Please replace the paragraph on page 28 at lines 7-16:

A photoresist film is applied to the core substrate, followed by exposure and development to thereby provide an opening of 600 μm in diameter and an opening corresponding to the predetermined wiring pattern (not shown). The copper foil laid bare at the opening of the photoresist film is etched away using an etching solution containing sodium sulfite and sulfuric acid. The photoresist film is delaminated away to obtain a core substrate having the exposed portion (301) as shown in Fig. 9 and the exposed portion corresponding to the predetermined wiring pattern (not shown).

Please replace the paragraph starting on page 33, line 24 through page 34, line 7:

A semiconductor element (270) is disposed at a position where it can be mounted on the semiconductor-mounting side, and the assembly is passed through a solder reflow furnace under the temperature condition of only melting the low-melting solder to thereby mount the semiconductor element. After filling an underfill material (300) into the mounted portion using a dispenser, thermal curing is conducted to obtain a semiconductor device using an FC-PGA type multi-layer printed wiring board on which a semiconductor element is mounted as is shown in Fig. 7.

Please insert the following paragraph starting on page 34, starting at line 8:

Fig. 7 also shows a metal cover pad (170), a semiconductor die made of silicon (280), and metallic connecting pads (290).